

## Motivation

Future information technologies will be realized by nanometer-scale (1 nm =  $10^{-9}$  m) semiconductor devices. In such devices, electron behavior is dominated by the quantum mechanics. Thus, real-space understanding and control of the nanometer-scale physics is very important to develop high-performance quantum devices through observing electron behavior directly in the nanostructures.

## Originality

Using scanning tunneling microscope (STM) at low-temperature, we succeeded to perform atom manipulation and *in-situ* characterization on the semiconductor surface. Coherently coupled electronic states of interacting adatoms was imaged. At the cross-section of semiconductor devices, such as the *p-n* junction and inversion layer, nanometer-scale energy band profiles were characterized. Semiconductor electronic states can be understood directly with controlling them at atomic scale.

## Impact

This technology will contribute to further understanding and control of quantum mechanical phenomena of electrons and holes in low-dimensional semiconductor structures designed for quantum devices and quantum computers.

